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Please note: As part of the Fairchild Semiconductor integration, some of the Fairchild orderable part numbers will need to change in order to meet ON Semiconductor's system requirements. Since the ON Semiconductor product management systems do not have the ability to manage part nomenclature that utilizes an underscore (_), the underscore (_) in the Fairchild part numbers will be changed to a dash (-). This document may contain device numbers with an underscore (_). Please check the ON Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.onsemi.com. Please email any questions regarding the system integration to Fairchild_questions@onsemi.com.

May 2014

FDMC7692

N-Channel Power Trench® MOSFET

30 V, 13.3 A, 8.5 mΩ

Features

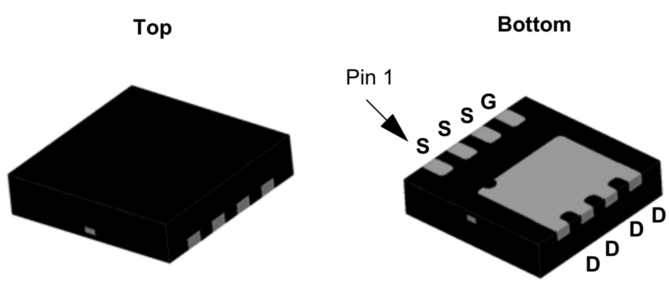
- Max $r_{DS(on)}$ = 8.5 mΩ at V_{GS} = 10 V, I_D = 13.3 A
- Max $r_{DS(on)}$ = 11.5 mΩ at V_{GS} = 4.5 V, I_D = 10.6 A
- High performance technology for extremely low $r_{DS(on)}$
- Termination is Lead-free and RoHS Compliant

General Description

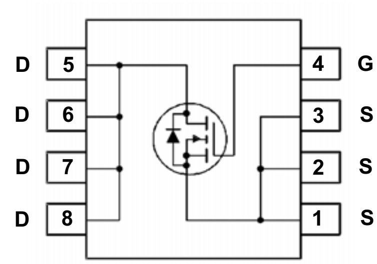
This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench® process that has been especially tailored to minimize the on-state resistance. This device is well suited for Power Management and load switching applications common in Notebook Computers and Portable Battery Packs.

Application

- DC - DC Buck Converters
- Notebook battery power management
- Load switch in Notebook



MLP 3.3x3.3



MOSFET Maximum Ratings T_A = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	±20	V
I_D	Drain Current -Continuous (Package limited) T_C = 25 °C	16	A
	-Continuous T_A = 25 °C (Note 1a)	13.3	
	-Pulsed	40	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	58	mJ
P_D	Power Dissipation T_C = 25 °C	29	W
	Power Dissipation T_A = 25 °C (Note 1a)	2.3	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	4.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	53	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMC7692	FDMC7692	MLP 3.3x3.3	13 ”	12 mm	3000 units

Electrical Characteristics T_J = 25 °C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain to Source Breakdown Voltage	I_D = 250 μA, V_{GS} = 0 V	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		16		mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 24 V, V_{GS} = 0 V			1	μA
		T_J = 125 °C			250	
I_{GSS}	Gate to Source Leakage Current	V_{GS} = 20 V, V_{DS} = 0 V			100	nA

On Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate to Source Threshold Voltage	V_{GS} = V_{DS}, I_D = 250 μA	1.2	1.9	3.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	I_D = 250 μA, referenced to 25 °C		-6		mV/°C
$r_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 13.3 A		7.2	8.5	mΩ
		V_{GS} = 4.5 V, I_D = 10.6 A		9.5	11.5	
		V_{GS} = 10 V, I_D = 13.3 A, T_J = 125 °C		9.5	12.0	
g_{FS}	Forward Transconductance	V_{DD} = 5 V, I_D = 13.3 A		60		S

Dynamic Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	V_{DS} = 15 V, V_{GS} = 0 V, f = 1 MHz		1260	1680	pF
C_{oss}	Output Capacitance			480	635	pF
C_{rss}	Reverse Transfer Capacitance			65	100	pF
R_g	Gate Resistance			0.9	2.4	Ω

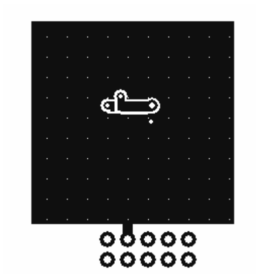
Switching Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 15 V, I_D = 13.3 A, V_{GS} = 10 V, R_{GEN} = 6 Ω		9	18	ns
t_r	Rise Time			4	10	ns
$t_{d(off)}$	Turn-Off Delay Time			21	33	ns
t_f	Fall Time			3	10	ns
$Q_{g(TOT)}$	Total Gate Charge	V_{GS} = 0 V to 10 V; V_{DD} = 15 V, I_D = 13.3 A		21	29	nC
	Total Gate Charge	V_{GS} = 0 V to 4.5 V; V_{DD} = 15 V, I_D = 13.3 A		10	14	nC
Q_{gs}	Total Gate Charge	V_{DD} = 15 V, I_D = 13.3 A		5		nC
Q_{gd}	Gate to Drain "Miller" Charge			3		nC

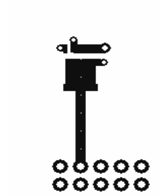
Drain-Source Diode Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_S = 13.3 A (Note 2)		0.86	1.2	V
		V_{GS} = 0 V, I_S = 1.9 A (Note 2)		0.75	1.2	
t_{rr}	Reverse Recovery Time	I_F = 13.3 A, di/dt = 100 A/μs		24	38	ns
Q_{rr}	Reverse Recovery Charge			7	14	nC

NOTES:
1. $R_{\theta JA}$ is determined with the device mounted on a 1 in^2 pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined by the user's board design.



a. 53 °C/W when mounted on a 1 in^2 pad of 2 oz copper



b.125 °C/W when mounted on a minimum pad of 2 oz copper

2. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0 %.
3. E_{AS} of 58 mJ is based on starting T_J = 25 °C, L = 1 mH, I_{AS} = 10.8 A, V_{DD} = 27 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 21 A.

Typical Characteristics T_J = 25 °C unless otherwise noted

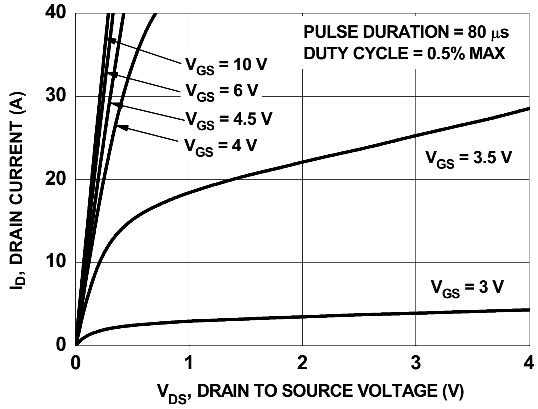


Figure 1. On-Region Characteristics

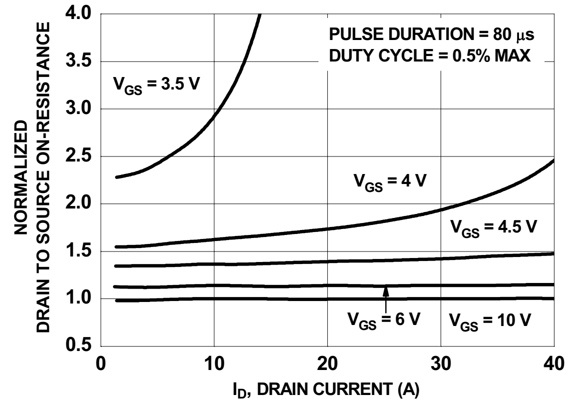


Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage

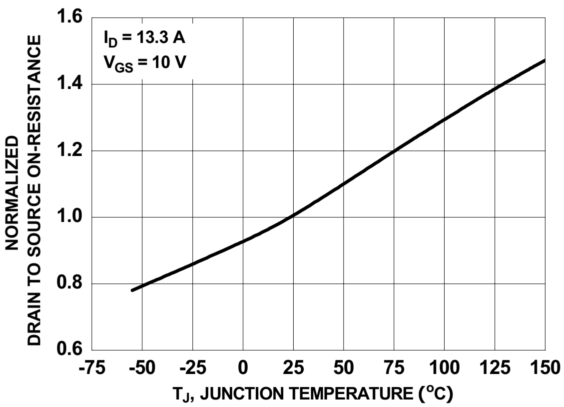


Figure 3. Normalized On-Resistance vs Junction Temperature

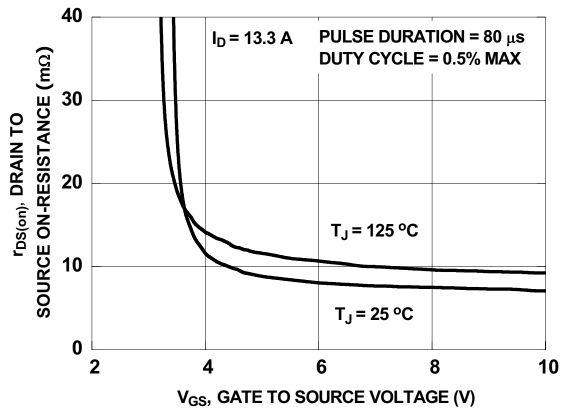


Figure 4. On-Resistance vs Gate to Source Voltage

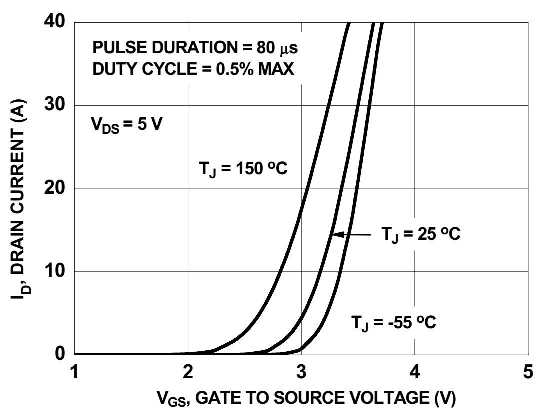


Figure 5. Transfer Characteristics

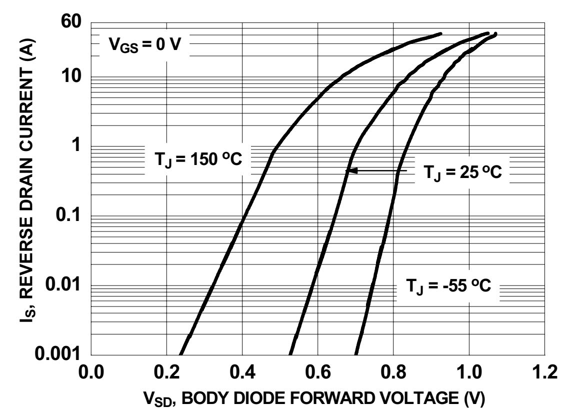


Figure 6. Source to Drain Diode Forward Voltage vs Source Current

Typical Characteristics T_J = 25 °C unless otherwise noted

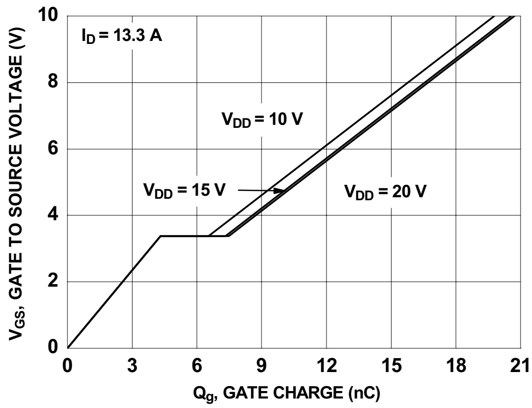


Figure 7. Gate Charge Characteristics

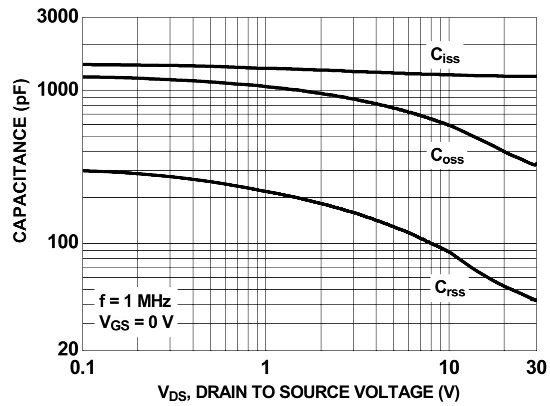


Figure 8. Capacitance vs Drain to Source Voltage

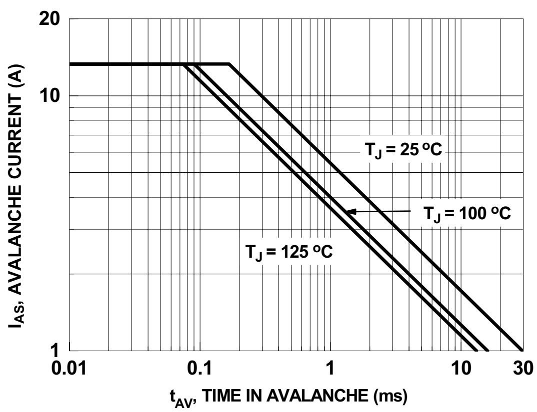


Figure 9. Unclamped Inductive Switching Capability

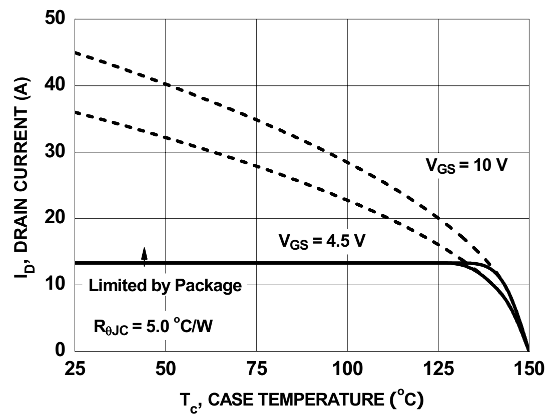


Figure 10. Maximum Continuous Drain Current vs Case Temperature

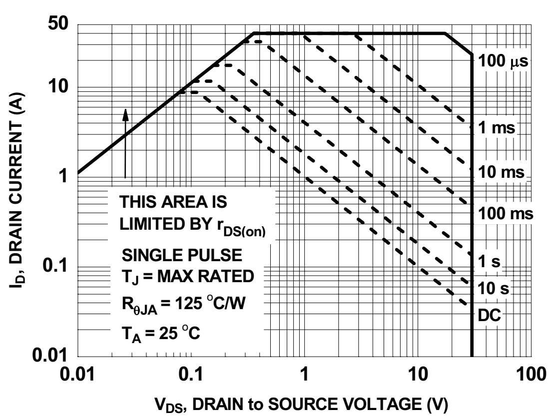


Figure 11. Forward Bias Safe Operating Area

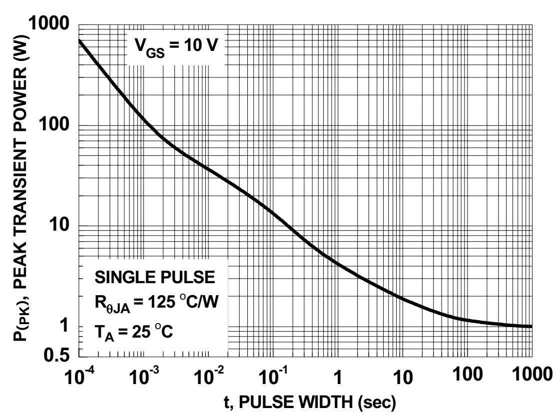


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics T_J = 25 °C unless otherwise noted

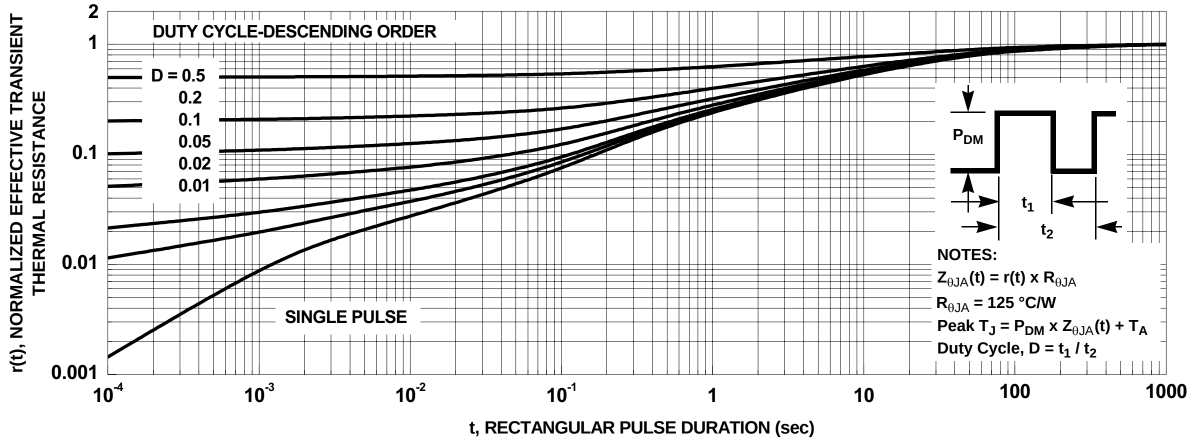
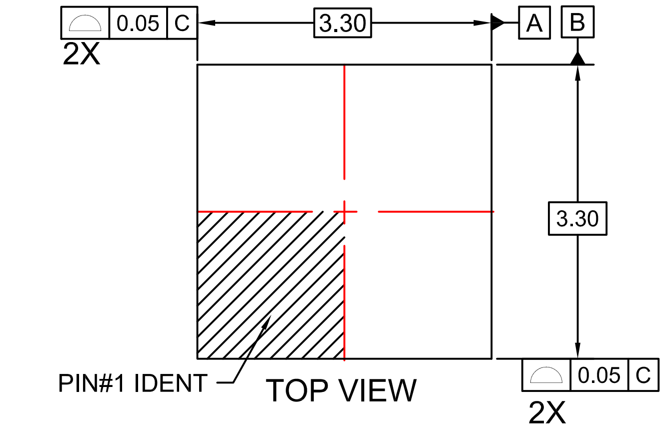
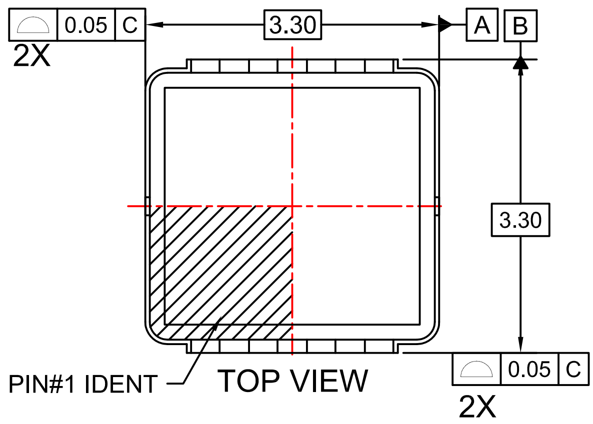


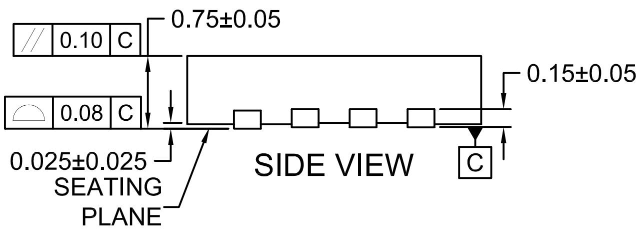
Figure 13. Transient Thermal Response Curve



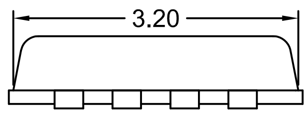
TOP VIEW



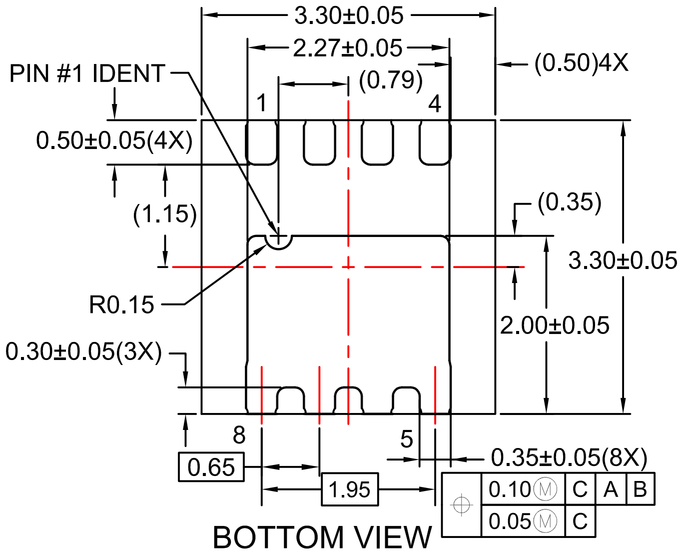
TOP VIEW



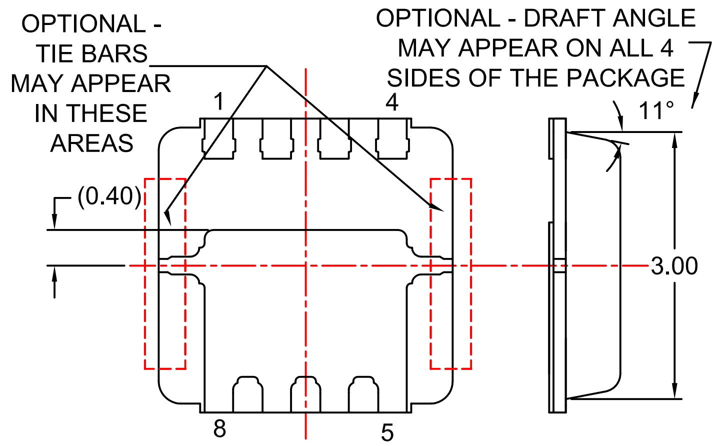
SIDE VIEW



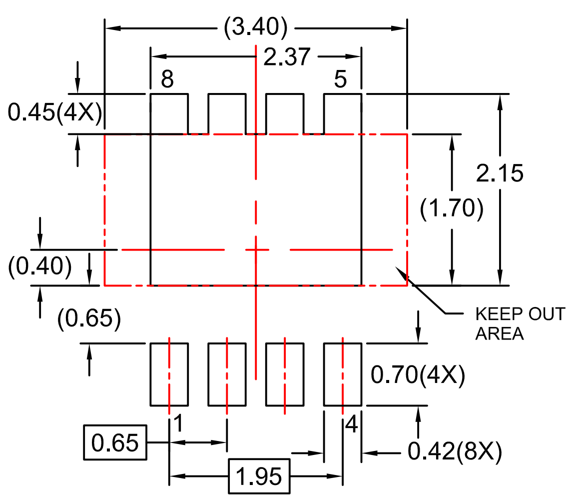
SIDE VIEW



BOTTOM VIEW
(OPTION A)

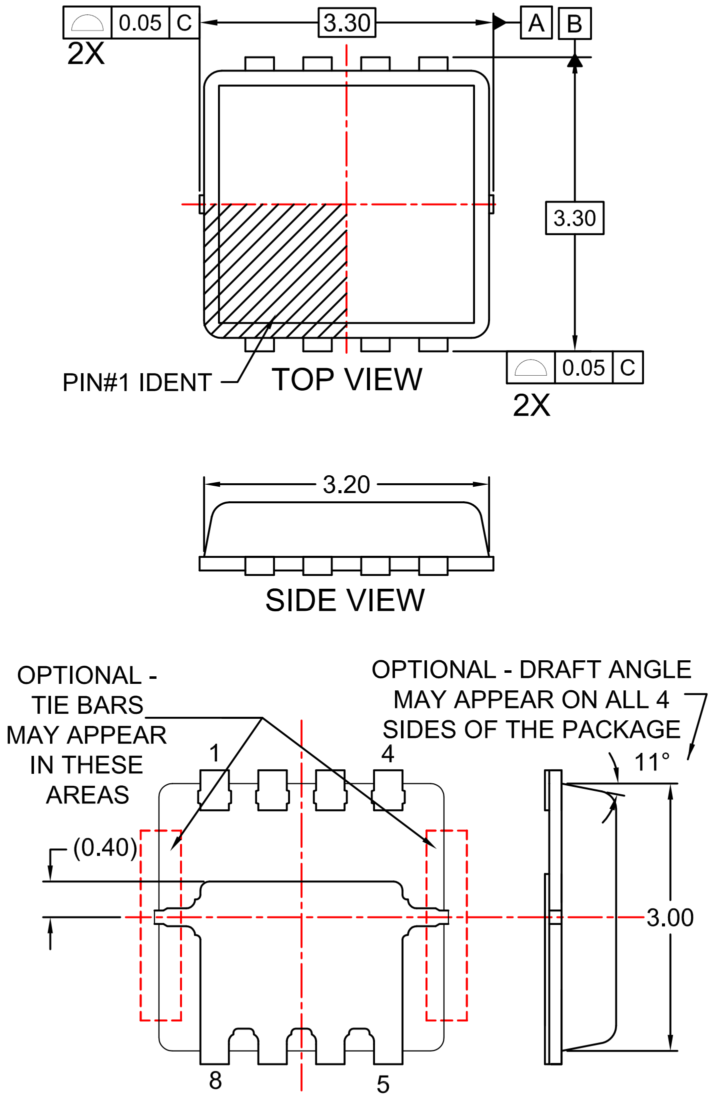


ALL DIMENSIONS AS PER OPTION A UNLESS SPECIFIED
BOTTOM VIEW
(OPTION B)



RECOMMENDED LAND PATTERN

FAIRCHILD



ALL DIMENSIONS AS PER OPTION A
UNLESS SPECIFIED

BOTTOM VIEW
(OPTION C)

NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN
E. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.
F. DRAWING FILENAME: MKT-MLP08Wrev3.
G. OPTION A - SAWN MLP, OPTIONS B & C - PUNCH MLP.

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